
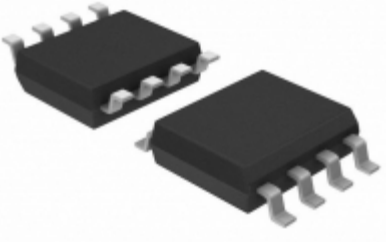
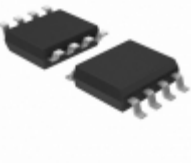




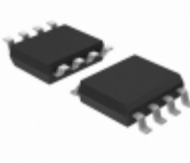

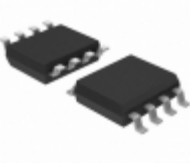
	<p>SI4172DY-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI4172DY-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET N-CH 30V 15A 8-SOIC</p> <p>Datenblätter:  SI4172DY-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 269156 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI4172DY-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET N-CH 30V 15A 8-SOIC
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	269156 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	8-SOIC (0.154", 3.90mm Width)
Supplier Device-Gehäuse	8-SO
Verlustleistung (max)	2.5W (Ta), 4.5W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	15A (Tc)
Rds On (Max) @ Id, Vgs	12 mOhm @ 11A, 10V
VGS (th) (Max) @ Id	2.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	23nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	820pF @ 15V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)



















































SI4172DY-T1-GE3 ist neu im Original, Suche SI4172DY-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI4172DY-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI4172DY-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI4170DY-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 30A 8-SOIC</p>	 <p>SI4172DY-T1 VISHAY VISHAY SO-8</p>	 <p>SI4172DY VISHAY SI4172DY VISHAY</p>	 <p>SI4172DY-T1-E3 V SI4172DY-T1-E3 V</p>
 <p>SI4174DY-T1-E3 V SI4174DY-T1-E3 V</p>	 <p>SI4174DY-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 17A 8-SOIC</p>	 <p>SI4174DY-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 17A 8-SOIC</p>	 <p>SI4172DY-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 15A 8-SOIC</p>

heiße Teile

Mehr

 SI4160DY-T1-E3	 SI4160DY-T1-GE3	 SI4160DY-T1-GE3	 SI4160DY-T1-GE3	 SI4162DY
 SI4162DY-T1-E3	 SI4162DY-T1-GE3	 SI4162DY-T1-GE3	 SI4164DY	 SI4164DY-T1-E3
 SI4164DY-T1-GE3	 SI4164DY-T1-GE3	 SI4166DY	 SI4166DY-T1-E3	 SI4166DY-T1-GE3
 SI4166DY-T1-GE3	 SI4168DY	 SI4168DY-T1-E3	 SI4168DY-T1-GE3	 SI4168DY-T1-GE3
 SI4170DY-T1-GE3	 SI4170DY-T1-GE3	 SI4172DY	 SI4172DY-T1-E3	 SI4172DY-T1-GE3
 SI4174DY	 SI4174DY-T1-E3	 SI4174DY-T1-GE3	 SI4174DY-T1-GE3	 SI4176DY-T1-GE3
 SI4176DY-T1-GE3	 SI4178DY	 SI4178DY-T1-E3	 SI4178DY-T1-E3	 SI4178DY-T1-GE3
 SI4178DY-T1-GE3	 SI4186DY-T1-E3	 SI4188DY-T1-E3	 SI4190ADY	 SI4196DY-T1-GE3
 SI4196DY-T1-GE3	 SI4200-BM	 SI4200-BMR	 SI4200-GM	 SI4200-GMR
 SI4200BM	 SI4200DB-BMR	 SI4200DY-T1-E3	 SI4201-BMR	 SI4201-GMR

Contact us: Info@Y-IC.com

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